TOSHIBA TRANSISTOR SILOCON NPN EPITAXIAL TYPE (PCT PROCESS)

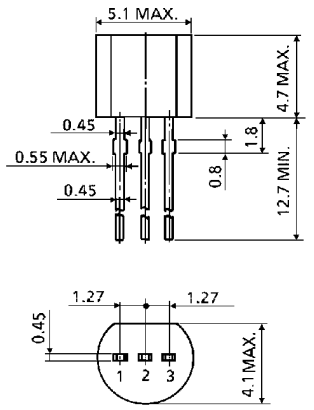
2SC2240

LOW NOISE AUDIO AMPLIFIER APPLICATIONS

Unit in mm

The 2SC2240 is a transistor for low frequency and low noise applications. This device is designed to lower noise figure in the region of low signal source impedance, and to lower the pulse noise. This is recommended for the first stages of Equalizer amplifiers.

- Low Noise
  : NF = 4dB (Typ.) R_G = 100Ω, V_{CE} = 6V, I_C = 100μA, f = 1kHz
  : NF = 0.5dB (Typ.) R_G = 1kΩ, V_{CE} = 6V, I_C = 100μA, f = 1kHz
- Low Pulse Noise : Low 1/f Noise
- High DC Current Gain : h_{FE} = 200~700
- High Breakdown Voltage : V_{CEO} = 120V



1. EMITTER
2. COLLECTOR
3. BASE

JEDEC	TO-92
EIAJ	SC-43
TOSHIBA	2-5F1B

Weight : 0.21g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Base Current	I_B	20	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB} = 120V, I_E = 0	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 5V, I_C = 0	—	—	0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 1mA, I_B = 0	120	—	—	V
DC Current Gain	h_{FE} (Note)	V_{CE} = 6V, I_C = 2mA	200	—	700	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 10mA, I_B = 1mA	—	—	0.3	V
Base-Emitter Voltage	V_{BE}	V_{CE} = 6V, I_C = 2mA	—	0.65	—	V
Transition Frequency	f_T	V_{CE} = 6V, I_C = 1mA	—	100	—	MHz
Collector Output Capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	—	3.0	—	pF
Noise Figure	NF	V_{CE} = 6V, I_C = 0.1mA, f = 10Hz, R_G = 10kΩ	—	—	6	dB
		V_{CE} = 6V, I_C = 0.1mA, f = 1kHz, R_G = 10kΩ	—	—	2	
		V_{CE} = 6V, I_C = 0.1mA, f = 1kHz, R_G = 100Ω	—	4	—	

Note : h_{FE} Classification GR : 200~400, BL : 350~700

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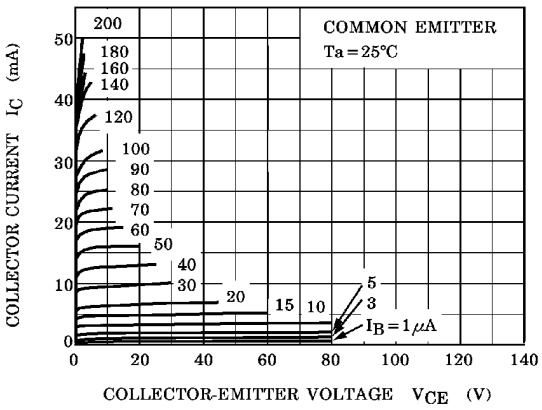
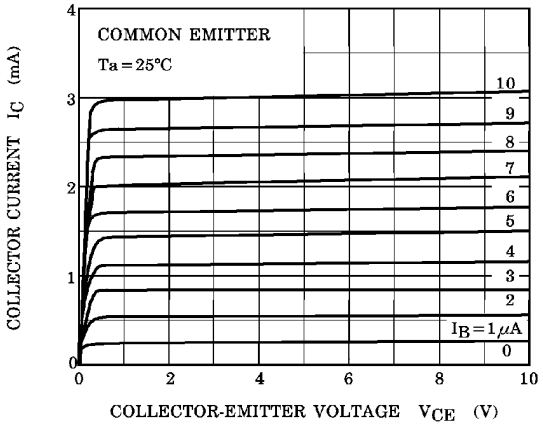
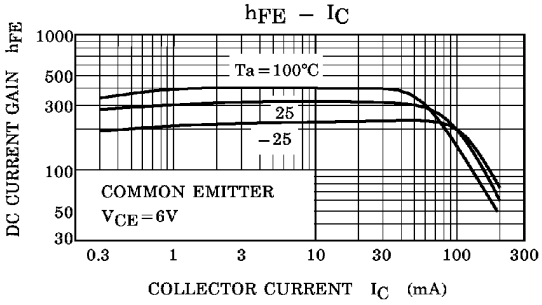
I_C – V_{CE}



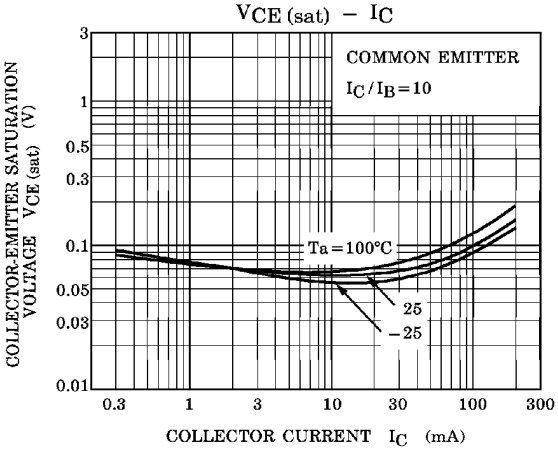
I_C – V_{CE}



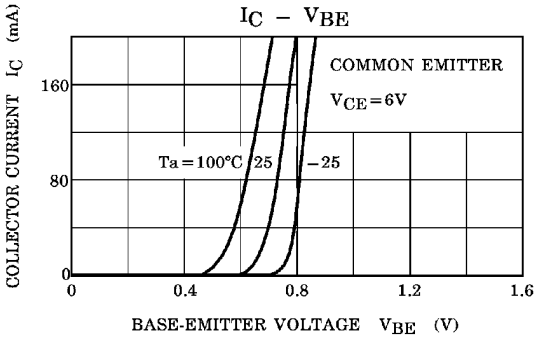
h_{FE} – I_C



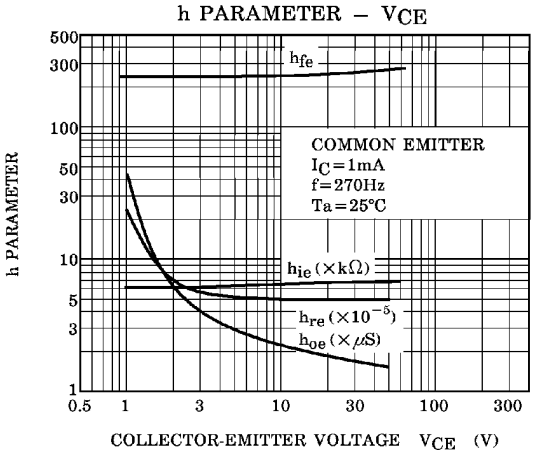
$V_{CE\,(sat)}$ – I_C



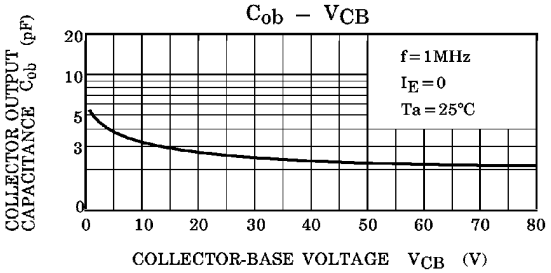
I_C – V_{BE}



h PARAMETER – V_{CE}



C_{ob} – V_{CB}



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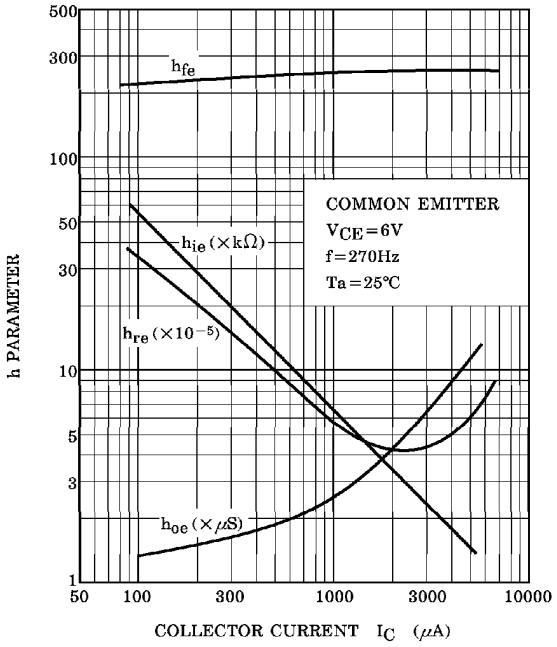
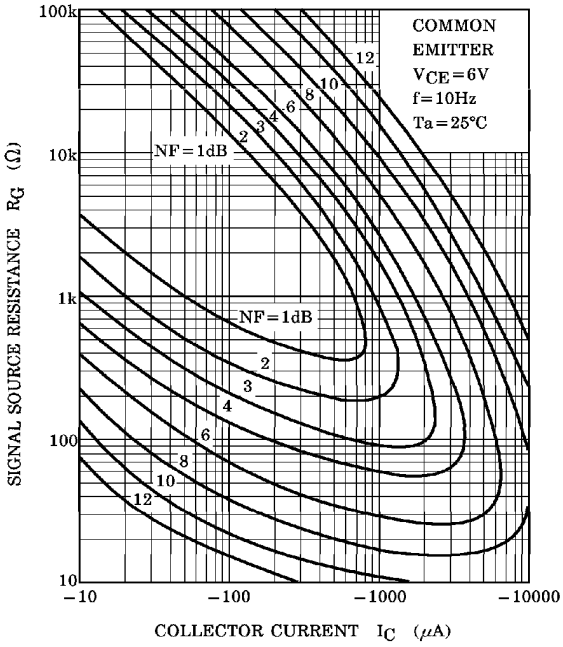
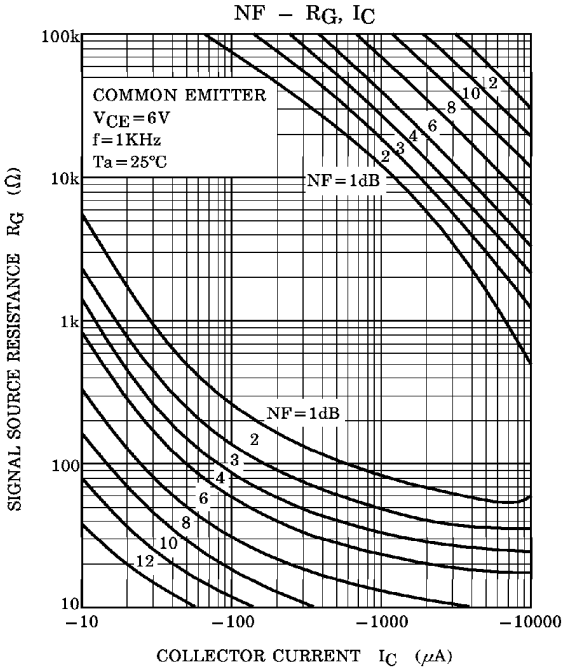
h PARAMETER – I_C



NF – R_G, I_C



NF – R_G, I_C



P_C – Ta